

1 K × 8 Dual-Port Static RAM

Features

- True dual-ported memory cells, which allow simultaneous reads of the same memory location
- 1 K x 8 organization
- 0.65 micron CMOS for optimum speed and power
- High speed access: 15 ns
- Low operating power: I_{CC} = 110 mA (maximum)
- Fully asynchronous operation
- Automatic power-down
- Master CY7C130/130A/CY7C131/131A easily expands data bus width to 16 or more bits using slave CY7C140/CY7C141
- BUSY output flag on CY7C130/130A/CY7C131/131A; BUSY input on CY7C140/CY7C141
- INT flag for port-to-port communication
- Available in 48-pin DIP (CY7C130/130A/140), 52-pin PLCC, 52-pin TQFP
- Pb-free packages available

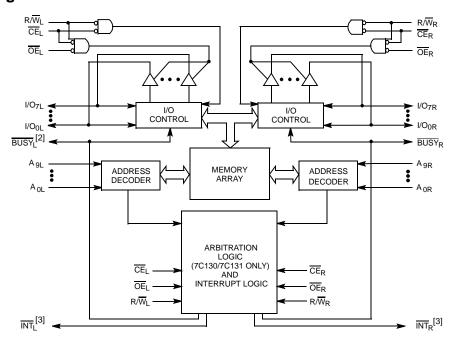
Functional Description

The CY7C130/130A/CY7C131/131A/CY7C140^[1] and CY7C141 are high speed CMOS 1 K by 8 dual-port static RAMs. Two ports are provided permitting independent access to any location in memory. The CY7C130/130A/CY7C131/131A can be used as either a standalone 8-bit dual-port static RAM or as a master dual-port RAM in conjunction with the CY7C140/CY7C141 slave dual-port device in systems requiring 16-bit or greater word widths. It is the solution to applications requiring shared or buffered data, such as cache memory for DSP, bit-slice, or multi-processor designs.

Each port <u>has</u> independent control <u>pins</u>; chip enable (\overline{CE}), write enable (R/W), <u>and</u> output enable (OE). Two flags are provided on each port, BUSY and INT. BUSY signals that the port is trying to access <u>the</u> same location currently being accessed by the other port. INT is an interrupt flag indicating that data is placed in a unique location (3FF for the left port and 3FE for the right port). An automatic power down feature <u>is</u> controlled independently on each port by the chip enable (CE) pins.

The CY7C130/130A and CY7C140 are available in 48-pin DIP. The CY7C131/131A and CY7C141 are available in 52-pin PLCC, 52-pin Pb-free PLCC, 52-pin PQFP, and 52-pin Pb-free PQFP.

Logic Block Diagram



Notes

- 1. CY7C130 and CY7C130A are functionally identical; CY7C131 and CY7C131A are functionally identical.
- CY7C130/130A/CY7C131/131A (Master): BUSY is open drain output and requires pull-up resistor. CY7C140/CY7C141 (Slave): BUSY is input.
- 3. Open drain outputs: pull-up resistor required.

CY7C130, CY7C130A CY7C131, CY7C131A



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Pin Configurations

Figure 1. Pin Diagram - DIP (Top View)

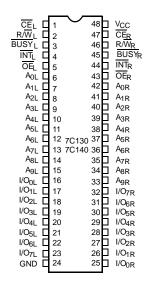


Figure 2. Pin Diagram - PLCC (Top View)

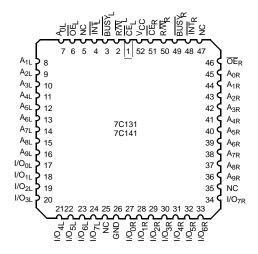
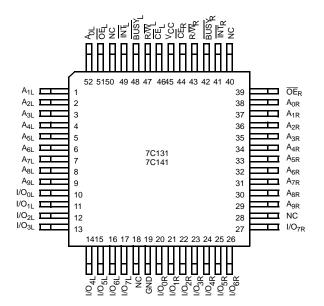


Figure 3. Pin Diagram - PQFP (Top View)





Pin Definitions

Left Port	Right Port	Description
CEL	CE _R	Chip enable
R/\overline{W}_L	R/\overline{W}_R	Read/write enable
OEL	OE _R	Output enable
A _{0L} -A _{11/12L}	A _{0R} -A _{11/12R}	Address
I/O _{0L} -I/O _{15/17L}	I/O _{0R} -I/O _{15/17R}	Data bus input/output
INT _L	INT _R	Interrupt flag
BUSY _L	BUSY _R	Busy flag
V _{CC}		Power
GND		Ground

Selection Guide

Parameter		7C131-15 ^[4] 7C131A-15 7C141-15	7C131-25 ^[4] 7C141-25	7C130-30 7C130A-30 7C131-30 7C140-30 7C141-30	7C130-35 7C131-35 7C140-35 7C141-35	7C130-45 7C131-45 7C140-45 7C141-45	7C130-55 7C131-55 7C140-55 7C141-55	Unit
Maximum access time	9	15	25	30	35	45	55	ns
Maximum operating Commercial current Industrial		190	170	170	120	120	110	mA
Maximum standby current	Commercial/ Industrial	75	65	65	45	45	35	mA

Shaded areas contain preliminary information.

Document Number: 38-06002 Rev. *H

Note
4. 15 and 25 ns version available only in PLCC/PQFP packages.



Maximum Ratings^[5]

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature-65 °C to +150 °C Ambient temperature with power applied -55 °C to +125 °C Supply voltage to ground potential (pin 48 to pin 24).....-0.5 V to +7.0 V DC voltage applied to outputs in high Z State.....-0.5 V to +7.0 V

DC input voltage	3.5 V to +7.0 V
Output current into outputs (LOW)	20 mA
Static discharge voltage(per MIL-STD-883, method 3015)	> 2001 V
Latch-up current	> 200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0 °C to +70 °C	5 V ± 10%
Industrial	–40 °C to +85 °C	5 V ± 10%
Military ^[6]	−55 °C to +125 °C	5 V ± 10%

Electrical Characteristics

Over the Operating Range^[7]

Parameter	Description	Test Conditions		7C13	1-15 ^[4] 31A-15 41-15	7C13 7C13 7C1	0-30 ^[4] 0A-30 1-25,30 40-30 1-25,30	7C13 ² 7C140	0-35,45 1-35,45 0-35,45 1-35,45	7C1:	30-55 31-55 40-55 41-55	Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
V _{OH}	Output HIGH voltage	$V_{CC} = Min, I_{OH} = -4.0$) mA	2.4	_	2.4	-	2.4	-	2.4	_	V
V_{OL}	Output LOW voltage	$I_{OL} = 4.0 \text{ mA}$		_	0.4	ı	0.4	_	0.4	-	0.4	V
		$I_{OL} = 16.0 \text{ mA}^{[8]}$		_	0.5	-	0.5	_	0.5	_	0.5	V
V _{IH}	Input HIGH voltage			2.2	-	2.2	_	2.2	_	2.2	_	V
V _{IL}	Input LOW voltage			-	0.8	_	0.8	_	0.8	_	0.8	V
I _{IX}	Input leakage current	$GND \le V_1 \le V_{CC}$		-5	+5	- 5	+5	- 5	+5	- 5	+5	μΑ
I _{OZ}	Output leakage current	$GND \le V_O \le V_{CC}$, out	tput disabled	- 5	+5	- 5	+5	- 5	+5	- 5	+5	μΑ
I _{OS}	Output short circuit current ^[9, 10]	V _{CC} = Max, V _{OUT} = GND		-	-350	_	-350	_	-350	-	-350	mA
I _{CC}	V _{CC} operating supply current	$CE = V_{IL}$, outputs open, $f = f_{MAX}^{[11]}$	Commercial	-	190	_	170	-	120	_	110	mA
I _{SB1}	Standby current both ports, TTL inputs	CE_L and $CE_R \ge V_{IH}$, $f = f_{MAX}^{[11]}$	Commercial	_	75	_	65	-	45	_	35	mA
I _{SB2}	Standby current one port, TTL inputs	CE _L or CE _R \geq V _{IH} , active port outputs open, f = f _{MAX} ^[11]	Commercial	_	135	-	115	_	90	-	75	mA
I _{SB3}	Standby current both ports, CMOS inputs	$\label{eq:bounds} \begin{split} & \underline{Bot}h \text{ ports CE}_L \text{ and } \\ & \underline{CE}_R \geq V_{CC} - 0.2 \text{ V}, \\ & V_{IN} \geq V_{CC} - 0.2 \text{ V} \\ & \text{ or } V_{IN} \leq 0.2 \text{ V}, \text{ f} = 0 \end{split}$	Commercial	-	15	_	15	_	15	-	15	mA
I _{SB4}	Standby current one port, CMOS inputs	$\begin{array}{l} \underline{One} \ port \ CE_L \ or \\ \overline{CE}_R \geq V_{CC} - 0.2 \ V, \\ V_{IN} \geq V_{CC} - 0.2 \ V \\ or \ V_{IN} \leq 0.2 \ V, \\ active \ port \ outputs \\ open, \ f = f_{MAX}^{[11]} \end{array}$	Commercial	_	125	l	105	-	85	-	70	mA

Shaded areas contain preliminary information.

Notes

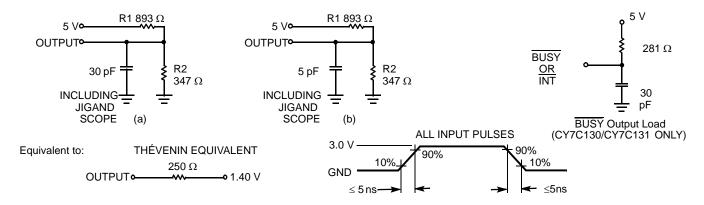
- 5. The voltage on any input or I/O pin cannot exceed the power pin during power up.
- 6. TA is the "instant on" case temperature
- See the last page of this specification for Group A subgroup testing information.
 BUSY and INT pins only.
- Duration of the short circuit should not exceed 30 seconds.
- 10. This parameter is guaranteed but not tested.
- 11. At f = f_{MAX}, address and data inputs are cycling at the maximum frequency of read cycle of 1/t_{RC} and using AC Test Waveforms input levels of GND to 3 V.



Capacitance^[10]

Parameter	Description	Test Conditions	Max	Unit
C _{IN}	Input capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz},$	15	pF
C _{OUT}	Output capacitance	$V_{CC} = 5.0 \text{ V}$	10	pF

Figure 4. AC Test Loads and Waveforms





Over the Operating Range^[12, 13]

Parameter	Description	7C13	I-15 ^[14] 1A-15 I1-15	7C130-25 ^[14] 7C131-25 7C140-25 7C141-25		7C130-30 7C130A-30 7C131-30 7C140-30 7C141-30		Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle		·						
t _{RC}	Read cycle time	15	_	25	_	30	_	ns
t _{AA}	Address to data valid ^[15]	_	15	_	25	_	30	ns
t _{OHA}	Data hold from address change	0	_	0	_	0	_	ns
t _{ACE}	CE LOW to data valid ^[15]	_	15	_	25	_	30	ns
t _{DOE}	OE LOW to data valid ^[15]	-	10	_	15	_	20	ns
t _{LZOE}	OE LOW to low Z ^[16, 17, 18]	3	_	3	_	3	_	ns
t _{HZOE}	OE HIGH to high Z ^[16, 17, 18]	_	10	_	15	_	15	ns
t _{LZCE}	CE LOW to low Z ^[16, 17, 18]	3	_	5	_	5	_	ns
t _{HZCE}	CE HIGH to high Z ^[16, 17, 18]	-	10	_	15	_	15	ns
t _{PU}	CE LOW to power-up ^[16]	0	_	0	_	0	_	ns
t _{PD}	CE HIGH to power-down ^[16]	-	15	_	25	_	25	ns
Write Cycle	19]	•		I.	I.	Į.	ı	
t _{WC}	Write cycle time	15	_	25	_	30	_	ns
t _{SCE}	CE LOW to write end	12	_	20	_	25	_	ns
t _{AW}	Address setup to write end	12	_	20	_	25	_	ns
t _{HA}	Address hold from write end	2	_	2	_	2	_	ns
t _{SA}	Address setup to write start	0	_	0	_	0	_	ns
t _{PWE}	R/W pulse width	12	_	15	_	25	_	ns
t _{SD}	Data setup to write end	10	_	15	_	15	_	ns
t _{HD}	Data hold from write end	0	_	0	_	0	_	ns
t _{HZWE}	R/\overline{W} LOW to high $Z^{[18]}$	_	10	_	15	_	15	ns
t _{LZWE}	R/\overline{W} HIGH to low $Z^{[18]}$	0	_	0	_	0	_	ns

Shaded areas contain preliminary information.

- 12. See the last page of this specification for Group A subgroup testing information.
- 13. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V and output loading of the specified I_{OL}/I_{OH}, and 30 pF load capacitance.

 14. 15 and 25 ns version available only in PLCC/PQFP packages.
- 15. AC Test Conditions use V_{OH} = 1.6 V and V_{OL} = 1.4 V. 16. This parameter is guaranteed but not tested.

- 17. At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZCE} and t_{HZOE} is less than t_{LZCE}.

 18. t_{LZCE}, t_{LZWE}, t_{HZOE}, t_{HZCE} and t_{HZWE} are tested with C_L = 5 <u>pF</u> as in part (b) <u>of AC</u> Test Loads. Transition is measured ±500 mV from steady state voltage.

 19. The internal write time of the memory is defined by the overlap of CS LOW and R/W LOW. Both signals must be low to initiate a write and either signal can terminate a write by going high. The data input setup and hold timing should be referenced to the rising edge of the signal that terminates the write.



Over the Operating Range^[12, 13] (continued)

Parameter	Description	7C13	1-15 ^[14] 1A-15 41-15	7C130-25 ^[14] 7C131-25 7C140-25 7C141-25		7C130-30 7C130A-30 7C131-30 7C140-30 7C141-30		Unit
		Min	Max	Min	Max	Min	Max	
Busy/Interru	pt Timing							
t _{BLA}	BUSY LOW from address match	_	15	_	20	_	20	ns
t _{BHA}	BUSY HIGH from address mismatch ^[20]	_	15	_	20	_	20	ns
t _{BLC}	BUSY LOW from CE LOW	_	15	_	20	_	20	ns
t _{BHC}	BUSY HIGH from CE HIGH ^[20]	_	15	_	20	_	20	ns
t _{PS}	Port set-up for priority	5	_	5	-	5	_	ns
t _{WB} ^[21]	R/W LOW after BUSY LOW	0	_	0	-	0	_	ns
t _{WH}	R/W HIGH after BUSY HIGH	13	_	20	-	30	_	ns
t _{BDD}	BUSY HIGH to valid data	-	15	_	25	_	30	ns
t _{DDD}	Write data valid to read data valid	_	Note 22	_	Note 22	_	Note 22	ns
t _{WDD}	Write pulse to data delay	_	Note 22	_	Note 22	_	Note 22	ns
Interrupt Tim	ing	.	1					
t _{WINS}	R/W to INTERRUPT set time	_	15	_	25	_	25	ns
t _{EINS}	CE to INTERRUPT set time	_	15	_	25	_	25	ns
t _{INS}	Address to INTERRUPT set time	-	15	_	25	_	25	ns
t _{OINR}	OE to INTERRUPT reset time ^[20]	_	15	_	25	_	25	ns
t _{EINR}	CE to INTERRUPT reset time ^[20]	-	15	_	25	_	25	ns
t _{INR}	Address to INTERRUPT reset time ^[20]	-	15	_	25	_	25	ns

Shaded areas contain preliminary information.

^{20.} These parameters are measured from the input signal changing, until the output pin goes to a high-impedance state.
21. CY7C140/CY7C141 only.
22. A write operation on Port A, where Port A has priority, leaves the data on Port B's outputs undisturbed until one access time after one of the following:
BUSY on Port B goes HIGH.

Port B's address is toggled.
CE for Port B is toggled.
R/W for Port B is toggled during valid read.



Over the Operating Range^[23, 24]

Parameter	Description	7C13	30-35 31-35 40-35 41-35	7C130-45 7C131-45 7C140-45 7C141-45		7C130-55 7C131-55 7C140-55 7C141-55		Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle								
t_{RC}	Read cycle time	35	_	45	_	55	_	ns
t_{AA}	Address to data valid ^[25]	_	35	_	45	_	55	ns
t _{OHA}	Data hold from address change	0	_	0	_	0	_	ns
t _{ACE}	CE LOW to data valid ^[25]	_	35	_	45	_	55	ns
t _{DOE}	OE LOW to data valid ^[25]	_	20	_	25	_	25	ns
t _{LZOE}	OE LOW to low Z ^[26, 27, 28]	3	_	3	_	3	_	ns
t _{HZOE}	OE HIGH to high Z ^[26, 27, 28]	_	20	_	20	_	25	ns
t _{LZCE}	CE LOW to low Z ^[26, 27, 28]	5	_	5	_	5	_	ns
t _{HZCE}	CE HIGH to high Z ^[26, 27, 28]	-	20	_	20	_	25	ns
t _{PU}	CE LOW to power-up ^[26]	0	_	0	_	0	_	ns
t _{PD}	CE HIGH to power-down ^[26]	-	35	_	35	_	35	ns
Write Cycle ^{[2}	29]	•						
t _{WC}	Write cycle time	35	_	45	_	55	_	ns
t _{SCE}	CE LOW to write end	30	_	35	_	40	_	ns
t _{AW}	Address set-up to write end	30	_	35	_	40	_	ns
t _{HA}	Address hold from write end	2	_	2	_	2	_	ns
t _{SA}	Address set-up to write start	0	_	0	_	0	_	ns
t _{PWE}	R/W pulse width	25	_	30	_	30	_	ns
t _{SD}	Data set-up to write end	15	_	20	_	20	_	ns
t _{HD}	Data hold from write end	0	_	0	_	0	_	ns
t _{HZWE}	R/W LOW to high Z ^[28]	_	20	_	20	_	25	ns
t _{LZWE}	R/W HIGH to low Z ^[28]	0	_	0	-	0	_	ns

^{23.} See the last page of this specification for Group A subgroup testing information.
24. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V and output loading of the specified I_{OL}/I_{OH}, and 30 pF load capacitance.
25. AC Test Conditions use V_{OH} = 1.6 V and V_{OL} = 1.4 V.
26. This parameter is guaranteed but not tested.

^{27.} At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZCE} and t_{HZOE} is less than t_{LZCE}.

28. t_{LZCE}, t_{LZWE}, t_{LZOE}, t_{LZOE}, t_{HZCE} and t_{HZWE} are tested with C_L = 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady state voltage.

29. The internal write time of the memory is defined by the overlap of CS LOW and R/W LOW. Both signals must be low to initiate a write and either signal can terminate a write by going high. The data input setup and hold timing should be referenced to the rising edge of the signal that terminates the write.



Over the Operating Range^[23, 24] (continued)

Parameter	Description	7C1 7C1	30-35 31-35 40-35 41-35	7C130-45 7C131-45 7C140-45 7C141-45		7C130-55 7C131-55 7C140-55 7C141-55		Unit	
		Min	Max	Min	Max	Min	Max		
Busy/Interru	ıpt Timing								
t _{BLA}	BUSY LOW from address match	_	20	_	25	_	30	ns	
t _{BHA}	BUSY HIGH from address mismatch ^[30]	_	20	-	25	_	30	ns	
t _{BLC}	BUSY LOW from CE LOW	_	20	-	25	_	30	ns	
t _{BHC}	BUSY HIGH from CE HIGH ^[30]	_	20	_	25	_	30	ns	
t _{PS}	Port set-up for priority	5	_	5	_	5	_	ns	
t _{WB} [31]	R/W LOW after BUSY LOW	0	_	0	_	0	_	ns	
t _{WH}	R/W HIGH after BUSY HIGH	30	_	35	_	35	_	ns	
t _{BDD}	BUSY HIGH to valid data	_	35	_	45	_	45	ns	
t _{DDD}	Write data valid to read data valid	_	Note 32	-	Note 32	_	Note 32	ns	
t _{WDD}	Write pulse to data delay	_	Note 32	-	Note 32	_	Note 32	ns	
Interrupt Tin	ning				•				
t _{WINS}	R/W to INTERRUPT set time	_	25	-	35	_	45	ns	
t _{EINS}	CE to INTERRUPT set time	_	25	-	35	-	45	ns	
t _{INS}	Address to INTERRUPT set time	_	25	-	35	-	45	ns	
t _{OINR}	OE to INTERRUPT reset time ^[20]	_	25	-	35	-	45	ns	
t _{EINR}	CE to INTERRUPT reset time ^[20]	_	25	-	35	-	45	ns	
t _{INR}	Address to INTERRUPT reset time ^[20]	_	25	-	35	-	45	ns	

Notes

^{30.} These parameters are measured from the input signal changing, until the output pin goes to a high-impedance state.

^{31.} CY7C140/CY7C141 only.

^{32.} A write operation on Port A, where Port A has priority, leaves the data on Port B's outputs undisturbed until one access time after one of the following: BUSY on Port B goes HIGH.

Port B's address is toggled.

CE for Port B is toggled.

R/W for Port B is toggled during valid read.



Switching Waveforms

Figure 5. Read Cycle No. $1^{[33, 34]}$

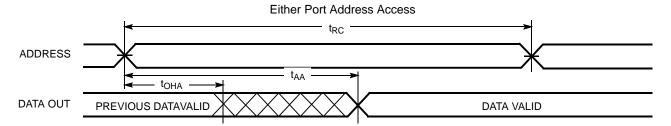


Figure 6. Read Cycle No. 2^[33, 35]

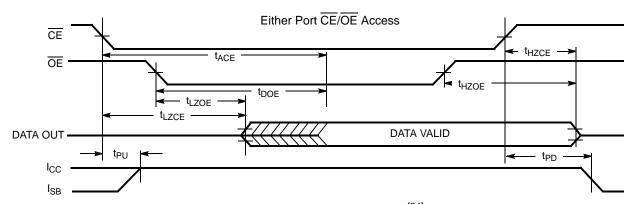
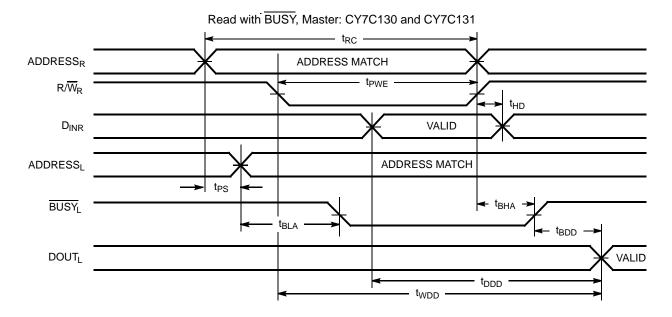


Figure 7. Read Cycle No. 3^[34]



- 33. R/W is HIGH for read cycle.
 34. Device is continuously selected, $\overline{CE} = V_{\parallel}$ and $\overline{OE} = V_{\parallel}$.
 35. Address valid prior to or coincident with \overline{CE} transition LOW.



Figure 8. Write Cycle No. 1 (OE Three-States Data I/Os—Either Port[36, 37]

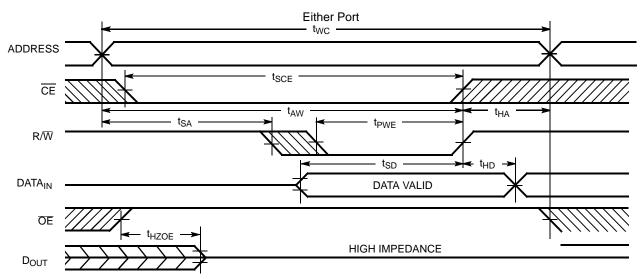
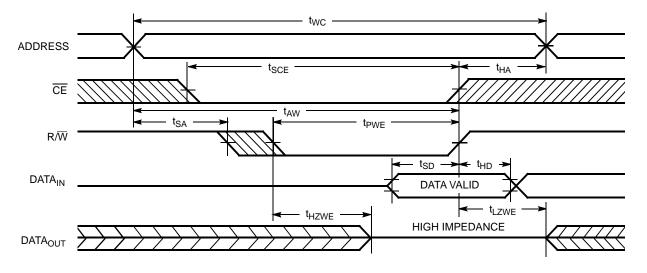


Figure 9. Write Cycle No. 2 (R/W Three-States Data I/Os—Either Port)[38, 39]



^{36.} The internal write time of the memory is defined by the overlap of $\overline{\text{CS}}$ LOW and R/W LOW. Both signals must be low to initiate a write and either signal can te<u>rmi</u>nate a write by going high. The data input setup and hold timing should be referenced to the rising edge of the signal that terminates the write.

^{37.} If OE is LOW during a RW controlled write cycle, the write pulse width must be the larger of t_{PWE} or t_{HZWE} + t_{SD} to allow the data I/O pins to enter high impedance and for data to be placed on the bus for the required t_{SD}.

38. These parameters are measured from the input signal changing, until the output pin goes to a high-impedance state.

39. If the CE LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the high impedance state.



Figure 10. Busy Timing Diagram No. 1 (CE Arbitration)

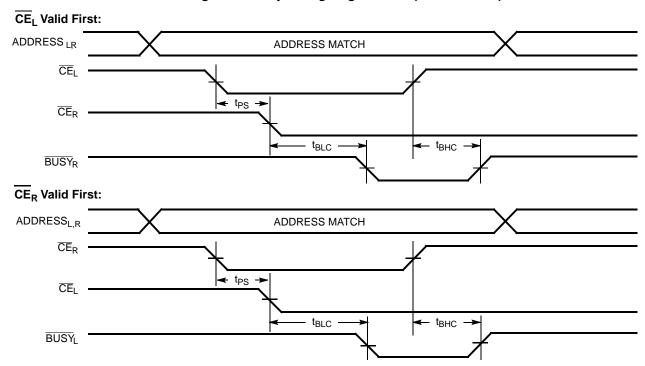


Figure 11. Busy Timing Diagram No. 2 (Address Arbitration)

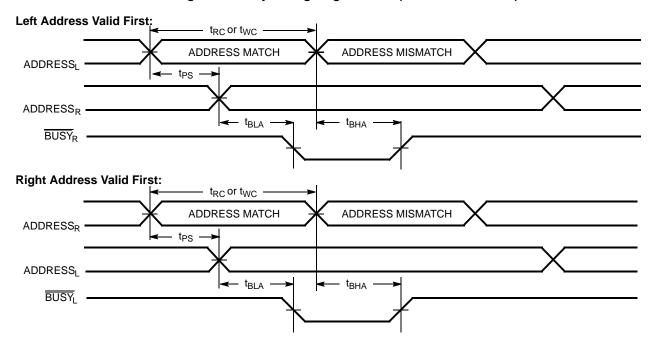




Figure 12. Busy Timing Diagram No. 3

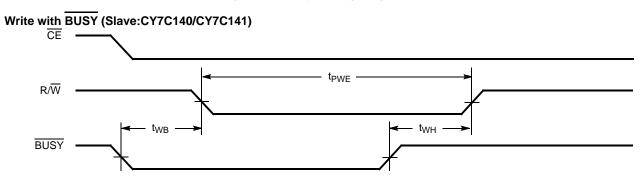
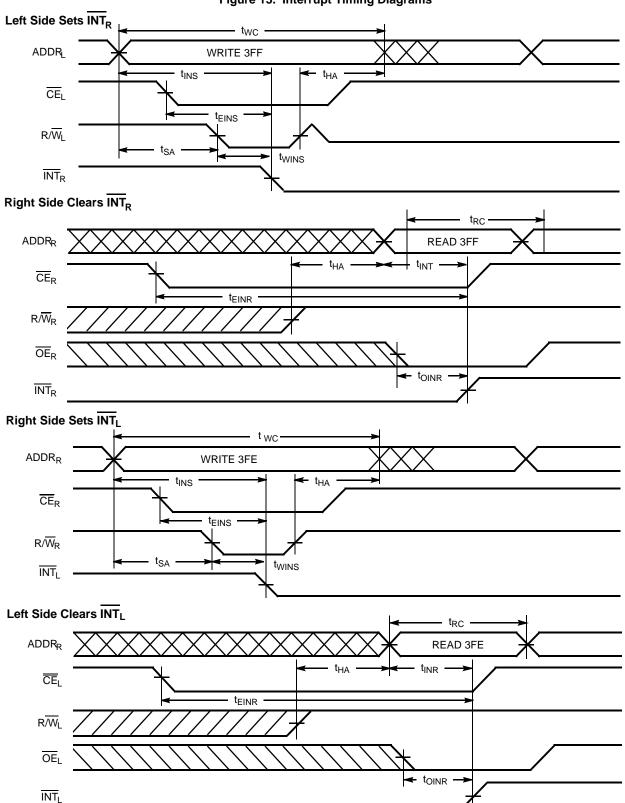


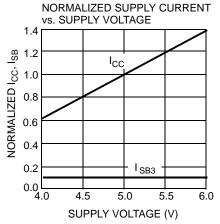


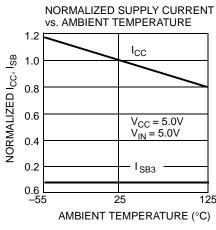
Figure 13. Interrupt Timing Diagrams

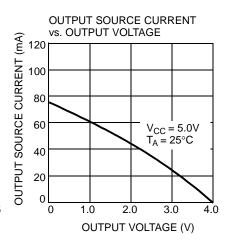


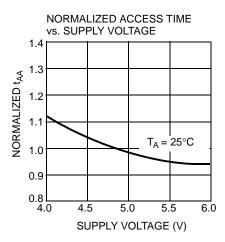


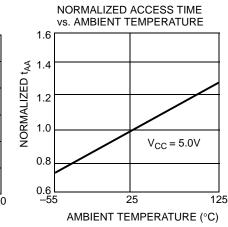
Typical DC and AC Characteristics

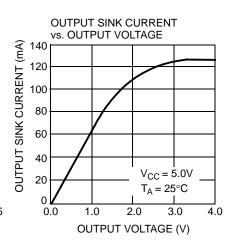


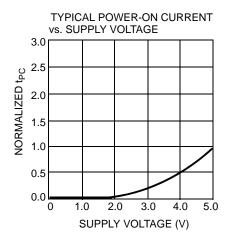


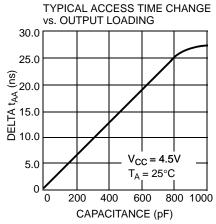


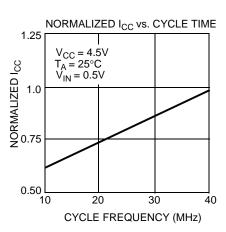










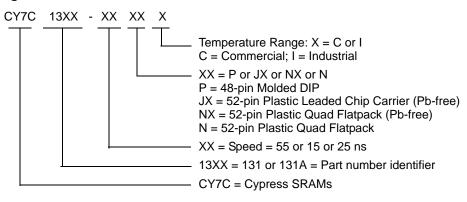




Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
55	CY7C130-55PC	P25	48-pin (600 Mil) Molded DIP	Commercial
15	CY7C131A-15JXI	J69	52-pin Pb-free Plastic Leaded Chip Carrier	Industrial
	CY7C131-15NXI	N52	52-pin Pb-free Plastic Quad Flatpack	
25	CY7C131-25JXC	J69	52-pin Pb-free Plastic Leaded Chip Carrier	Commercial
	CY7C131-25NXC	N52	52-pin Pb-free Plastic Quad Flatpack	
55	CY7C131-55JXC	J69	52-pin Pb-free Plastic Leaded Chip Carrier	Commercial
	CY7C131-55NXC	N52	52-pin Pb-free Plastic Quad Flatpack	
	CY7C131-55JXI	J69	52-pin Pb-free Plastic Leaded Chip Carrier	Industrial
	CY7C131-55NXI	N52	52-pin Pb-free Plastic Quad Flatpack	

Ordering Code Definitions

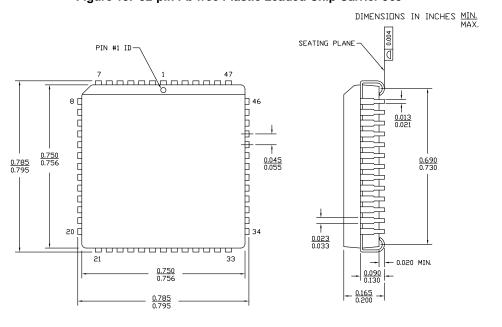




Package Diagrams

Figure 14. 48-pin (600 Mil) Sidebraze DIP D26 DIMENSIONS IN INCHES MIN. <u>.550</u> MAX. .610 .005 MIN. .080 BASE PLANE 2.370 2.430 .005 MIN. .008 -.150 MIN. .040 .012 .060 .590 .620 .015 .030 .022 SEATING PLANE

Figure 15. 52-pin Pb-free Plastic Leaded Chip Carrier J69



51-85004 *C

51-80044 *B



Package Diagrams (continued)

Figure 16. 48-pin (600 Mil) Molded DIP P25

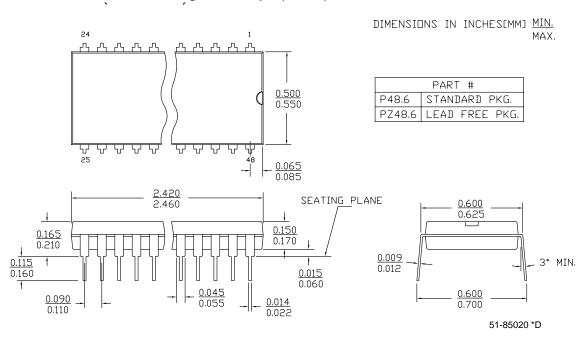
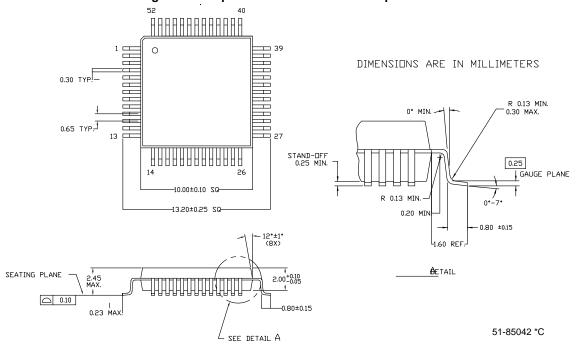


Figure 17. 52-pin Pb-free Plastic Quad Flatpack N52





Acronyms

Acronym	Description		
CE	chip enable		
CMOS	complementary metal oxide semiconductor		
DIP	dual in-line package		
I/O	input/output		
OE	output enable		
PLCC	plastic leaded chip carrier		
PQFP	plastic quad flat pack		
SRAM	static random access memory		
TQFP	thin quad flat pack		
TTL	Transistor-transistor logic		

Document Conventions

Units of Measure

Symbol	Unit of Measure
C	degree Celcius
MHz	megahertz
μΑ	microamperes
mA	milliamperes
ms	milliseconds
mV	millivolts
ns	nanoseconds
pF	picofarad
V	volts
W	watts



Document History Page

Oocument Title: CY7C130/CY7C130A/CY7C131/CY7C131A 1K x 8 Dual-Port Static RAM Oocument Number: 38-06002					
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change	
**	110169	SZV	09/29/01	Change from Spec number: 38-00027 to 38-06002	
*A	122255	RBI	12/26/02	Power up requirements added to Maximum Ratings Information	
*B	236751	YDT	See ECN	Removed cross information from features section	
*C	325936	RUY	See ECN	Added pin definitions table, 52-pin PQFP package diagram and Pb-free information	
*D	393153	YIM	See ECN	Added CY7C131-15JI to ordering information Added Pb-Free parts to ordering information: CY7C131-15JXI	
*E	2623540	VKN/PYRS	12/17/08	Added CY7C130A and CY7C131A parts Removed military information Updated ordering information table	
*F	2897217	RAME	03/22/2010	Updated Ordering Information Updated Package Diagrams	
*G	3054633	ADMU	10/11/2010	Updated Ordering Information and added Ordering Code Definitions. Updated Package Diagrams. Added Acronyms and Units of Measure. Minor edits and updated in new template.	
*H	3402163	ADMU	10/12/2011	Removed pruned part CY7C131-25NC from Ordering Information Updated Package Diagrams.	

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